

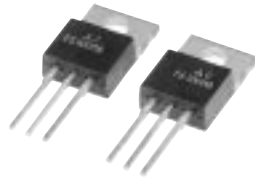
PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

FS10UMA-5A

HIGH-SPEED SWITCHING USE

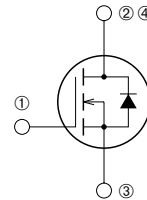
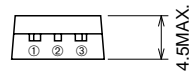
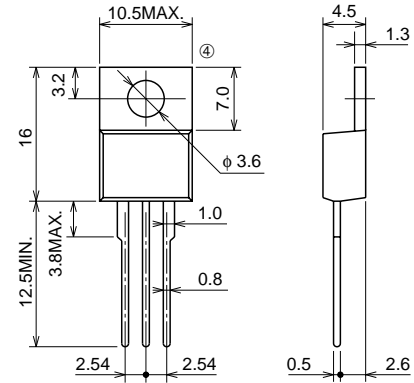
FS10UMA-5A



- 10V DRIVE
- V_{DSS} 250V
- $r_{DS(ON)}(MAX)$ 0.52Ω
- I_D 10A

OUTLINE DRAWING

Dimensions in mm



- ① GATE
- ② DRAIN
- ③ SOURCE
- ④ DRAIN

TO-220

APPLICATION

Cs Switch for CRT Display monitor

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	250	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		10	A
I_{DM}	Drain current (Pulsed)		30	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 200\mu H$	10	A
P_D	Maximum power dissipation		55	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	2.0	g

Sep.1998

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ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	250	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±10	μA
IDSS	Drain-source leakage current	VDS = 250V, VGS = 0V	—	—	1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	2.0	3.0	4.0	V
rDS (ON)	Drain-source on-state resistance	Id = 5A, VGS = 10V	—	0.40	0.52	Ω
VDS (ON)	Drain-source on-state voltage	Id = 5A, VGS = 10V	—	2.00	2.60	V
yfs	Forward transfer admittance	Id = 5A, VDS = 10V	—	9.0	—	S
Ciss	Input capacitance	VDS = 25V, VGS = 0V, f = 1MHz	—	950	—	pF
Coss	Output capacitance		—	90	—	pF
Crss	Reverse transfer capacitance		—	25	—	pF
td (on)	Turn-on delay time		—	20	—	ns
tr	Rise time	VDD = 150V, Id = 5A, VGS = 10V, RGEN = RGS = 50Ω	—	25	—	ns
td (off)	Turn-off delay time		—	150	—	ns
tf	Fall time		—	40	—	ns
VSD	Source-drain voltage	IS = 5A, VGS = 0V	—	0.95	—	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	2.27	°C/W